

## ABSTRACT OF THE DISCLOSURE

A semiconductor laminating portion including a light emitting layer forming portion having at least an n-type layer and a p-type layer is formed on a semiconductor substrate. A current blocking layer is partially formed on its surface. A current diffusing electrode is formed on the entire surface thereof. A bonding electrode is formed thereon. The semiconductor laminating portion and the current diffusing electrode are separated into light emitting unit portions A, electrode pad portion B, and connecting portions C for connecting between electrode pad portion B and light emitting unit portions A or between two of the light emitting unit portions A, and the semiconductor laminating portion between the light emitting unit portions A is removed through etching to make clearances except for connecting portions C. The bonding electrode is formed on electrode pad portion B.